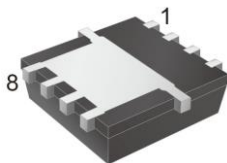


TSM180N03PQ33

30V N-Channel Power MOSFET

PDFN33



Pin Definition:

- | | |
|-----------|----------|
| 1. Source | 8. Drain |
| 2. Source | 7. Drain |
| 3. Source | 6. Drain |
| 4. Gate | 5. Drain |

Note:

MSL 1 (Moisture Sensitivity Level)
per J-STD-020

Key Parameter Performance

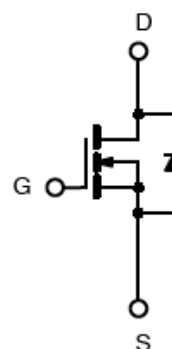
Parameter		Value	Unit
V_{DS}		30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	18	mΩ
	$V_{GS} = 4.5V$	28	
Q_g		4.1	nC

Ordering Information

Part No.	Package	Packing
TSM180N03PQ33 RGG	PDFN33	5Kpcs / 13" Reel

- Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	25	A
		16	A
Pulsed Drain Current ^(Note 1)	I_{DM}	100	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	32	mJ
Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	21	W
Operating Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance - Junction to Case	$R_{\theta JC}$	6	$^\circ\text{C/W}$

Electrical Specifications ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	30	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 12A$	$R_{DS(ON)}$	--	14	18	mΩ
	$V_{GS} = 4.5V, I_D = 8A$		--	20	28	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	1.2	1.6	2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
	$V_{DS} = 24V, T_J = 125^{\circ}C$		--	--	10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Forward Transconductance ^(Note 3)	$V_{DS} = 10V, I_D = 6A$	g_{fs}	--	6.5	--	S
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = 15V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_g	--	4.1	--	nC
Gate-Source Charge ^(Note 3,4)		Q_{gs}	--	1	--	
Gate-Drain Charge ^(Note 3,4)		Q_{gd}	--	2.1	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	345	--	pF
Output Capacitance		C_{oss}	--	55	--	
Reverse Transfer Capacitance		C_{rss}	--	32	--	
Switching						
Turn-On Delay Time ^(Note 3,4)	$V_{DD} = 15V, I_D = 1A,$ $V_{GS} = 10V, R_G = 6\Omega$	$t_{d(on)}$	--	2.8	--	ns
Turn-On Rise Time ^(Note 3,4)		t_r	--	7.2	--	
Turn-Off Delay Time ^(Note 3,4)		$t_{d(off)}$	--	15.8	--	
Turn-Off Fall Time ^(Note 3,4)		t_f	--	4.6	--	
Source-Drain Diode Ratings and Characteristic						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	25	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	100	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = 1A$	V_{SD}	--	--	1	V

Note:

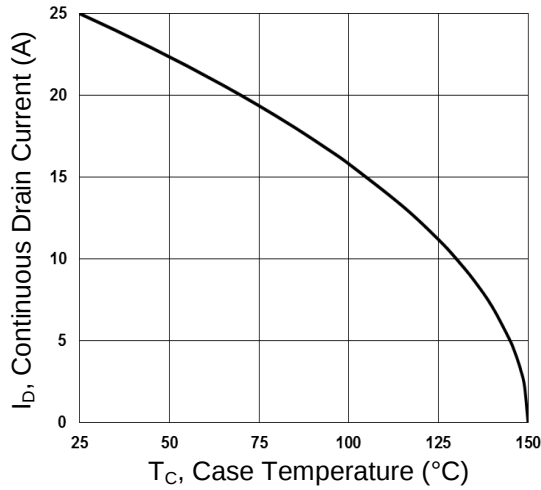
- Pulse width limited by safe operating area
- $L = 1\text{mH}, I_{AS} = 8A, V_{DD} = 25V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- Switching time is essentially independent of operating temperature.

TSM180N03PQ33

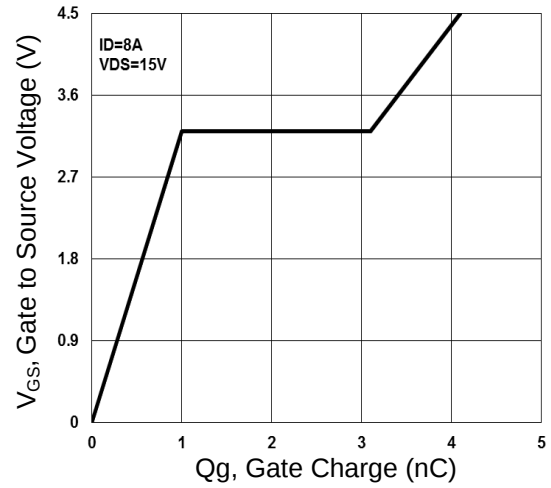
30V N-Channel Power MOSFET

Electrical Characteristics Curve

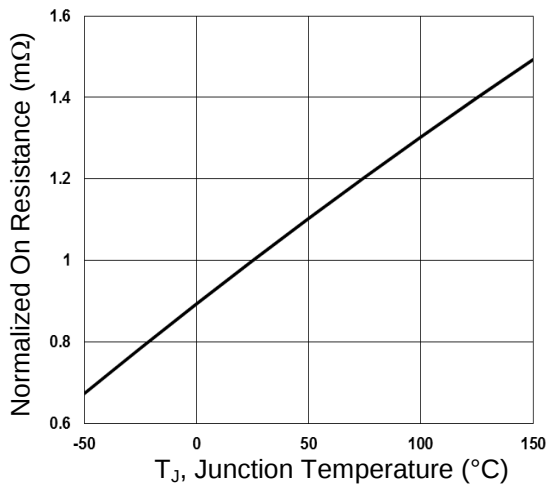
Continuous Drain Current vs. T_C



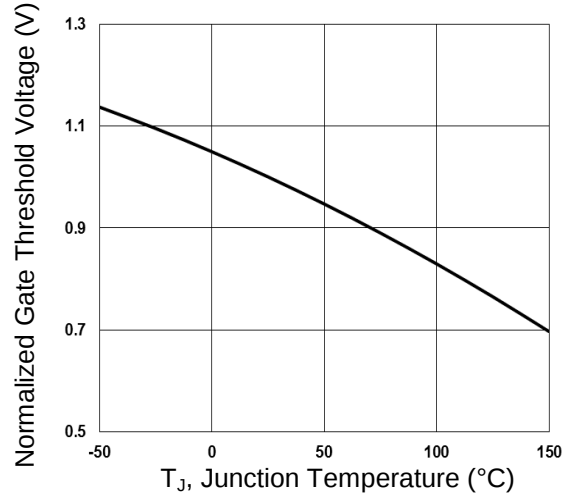
Gate Charge



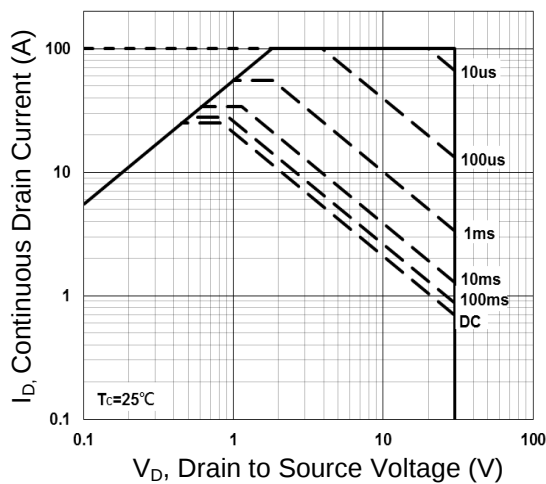
On-Resistance vs. Junction Temperature



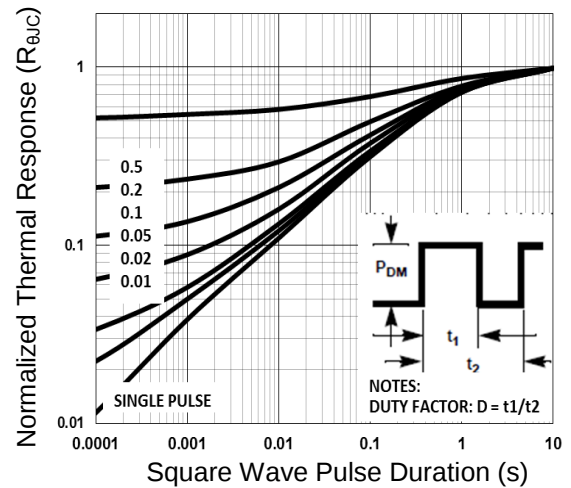
Threshold Voltage vs. Junction Temperature



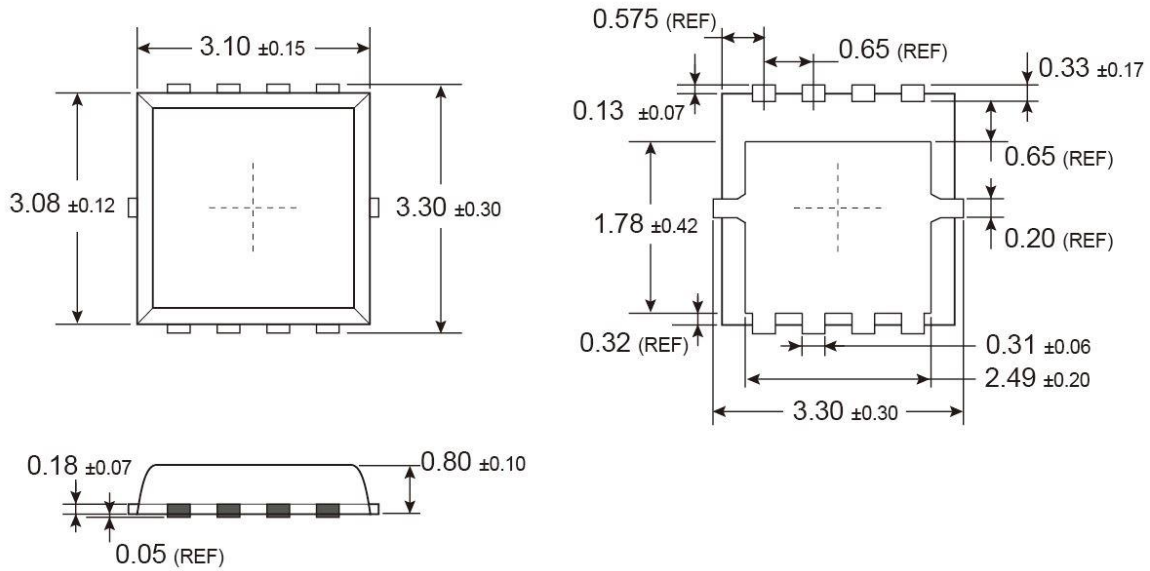
Maximum Safe Operating Area



Normalized Thermal Transient Impedance Curve

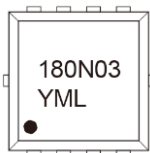


PDFN33 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

TSM180N03PQ33

30V N-Channel Power MOSFET

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